S-8243A/B Series

BATTERY PROTECTION IC FOR 3-SERIAL OR 4-SERIAL CELL PACK

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SII

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Rev.3.0_00

The S-8243A/B Series is a protection IC for lithium-ion rechargeable battery. The S-8243A Series protects 3-series, the S-8243B Series protects 4-series cell pack from the overcharge, overdischarge, overcurrent voltages. This IC has a high-accuracy battery protection circuit and a battery monitor amplifier, and also a voltage regulator which operates the microcomputer or gas gauge IC. Combining this IC and a microcomputer or a gas gauge IC allows to display the amount of charge remained in a battery.

Fea	itures		
(1)	High-accuracy voltage detection for each of	cell	
	 Overcharge detection voltage n (n = 1 t 	o 4)	
	3.9 V to 4.4 V (50 mV step)		Accuracy $\pm 25 \text{ mV}$
	• Hysteresis voltage n (n = 1 to 4) of over	charge detection	
	–0.10 V to –0.40 V (50 mV step) of	or 0 V	Accuracy ±50 mV
	(Overcharge release voltage n (= Over	charge detection voltage n + Hyst	teresis voltage n) can be selected within
	the range 3.8 V to 4.4 V.)		
	 Overdischarge detection voltage n (n = 	1 to 4)	
	2.0 V to 3.0 V (100 mV step)		Accuracy ±80 mV
	• Hysteresis voltage n (n = 1 to 4) of over	discharge detection	
	0.15 V to 0.70 V or 0 V (50 mV st	ep)	Accuracy ±100 mV
	(Overdischarge release voltage n (= Ov	verdischarge detection voltage n	+ Hysteresis voltage n) can be selected
	within the range 2.0 V to 3.4 V.)		
(2)	Three-level overcurrent protection includin	g protection for short-circuiting	
	 Overcurrent detection voltage 1 	0.05 V to 0.3 V (50 mV step)	Accuracy ±25 mV
	 Overcurrent detection voltage 2 	0.5 V	Accuracy ±100 mV
	 Overcurrent detection voltage 3 	V _{DD} / 2	Accuracy ±15 %
(3)	Delay times for overcharge detection, overc	lischarge detection and overcurre	ent detection 1 can be set by external
	capacitors. (Delay times for overcurrent det	ection 2 and 3 are fixed internally	<i>ı</i> .)
(4)	Charge/discharge operation can be contro	lled through the control pins.	
(5)	High-accuracy battery monitor amp	$GAMP = V_{BATTERY} \times 0.2$	±1.0%
(6)	Voltage regulator	$V_{OUT} = 3.3 \text{ V} \pm 2.4 \%$ (3)	mA max.)
(7)	High input-voltage device	Absolute maximum ratin	ng: 26 V
(8)	Wide operating voltage range	6 V to 18 V	
(9)	Wide operating temperature range:	−40 °C to +85°C	
(10)	Low current consumption		
	 Operation mode 	120 μA max.	
	Power down mode	0.1 μA max.	
(11)	Lead-free, Sn 100%, halogen-free ^{*1}		

*1. Refer to "
Product Name Structure" for details.

Applications

• Lithium-ion rechargeable battery packs

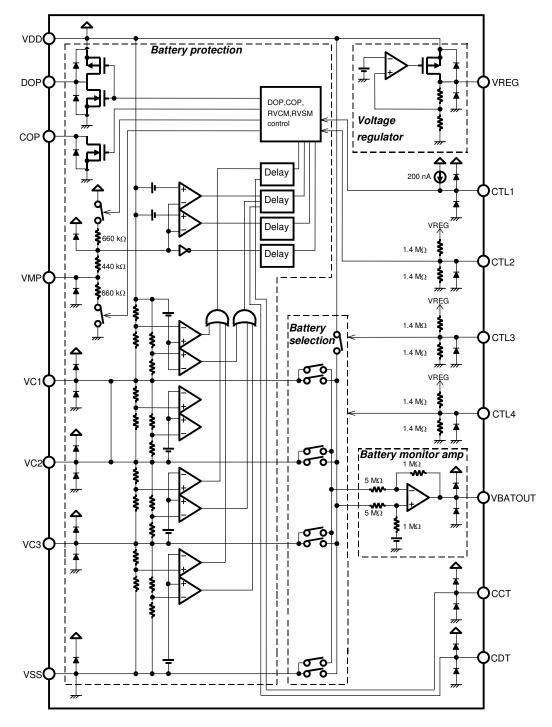
• Lithium polymer rechargeable battery packs

Package

• 16-Pin TSSOP

Block Diagrams

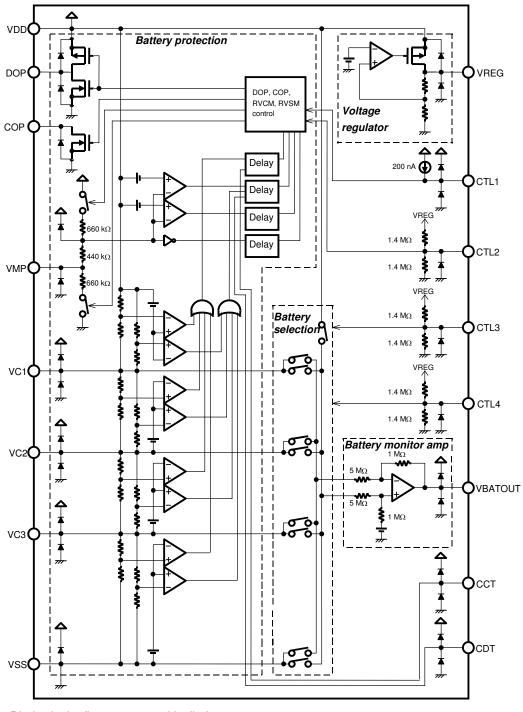
1. S-8243A Series



Remark1. Diodes in the figure are parasitic diodes.2. Numerical values are typical values.

Figure 1

2. S-8243B Series

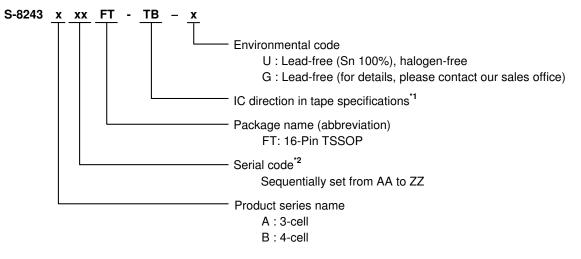


Remark1. Diodes in the figure are parasitic diodes.2. Numerical values are typical values.

Figure 2

Product Name Structure

1. Product Name



- *1. Refer to the tape specifications at the end of this book.
- *2. Refer to the "3. Product Name List".

2. Package

De	ackage Name	Drawing Code					
Γc	ackage Name	Package	Таре	Reel			
16-Pin TSSOP	Environmental code = G	FT016-A-P-SD	FT016-A-C-SD	FT016-A-R-SD			
10-FIII 1350P	Environmental code = U	FT016-A-P-SD	FT016-A-C-SD	FT016-A-R-S1			

3. Product Name List

Table 1 S-8243A Series (For 3-Serial Cell)

Product name / Item	Overcharge detection voltage [V _{CU}]	Hysteresis voltage for overcharge detection [V _{HC}]	Overdischarge detection voltage [V _{DL}]	Hysteresis voltage for overdischarge detection [V _{HD}]	Overcurrent detection voltage1 [V _{IOV1}]	0 V battery charging function
S-8243AACFT-TB-x	4.350 ±0.025 V	-0.15 ±0.05 V	2.40 ±0.08 V	0.20 ±0.10 V	0.20 ±0.025 V	Available
S-8243AADFT-TB-x	4.350 ±0.025 V	–0.35 ±0.05 V	2.40 ±0.08 V	0 V	0.20 ±0.025 V	Available

Product name / Item	Overcharge detection voltage [V _{CU}]	Hysteresis voltage for overcharge detection [V _{HC}]	Overdischarge detection voltage [V _{DL}]	Hysteresis voltage for overdischarge detection [V _{HD}]	Overcurrent detection voltage1 [V _{IOV1}]	0 V battery charging function
S-8243BADFT-TB-x	4.350 ±0.025 V	-0.25 ±0.05 V	2.40 ±0.08 V	0 V	0.25 ±0.025 V	Available
S-8243BAEFT-TB-x	4.350 ±0.025 V	-0.15 ±0.05 V	2.40 ±0.08 V	0.20 ±0.10 V	0.20 ±0.025 V	Available
S-8243BAFFT-TB-x	4.250 ±0.025 V	-0.25 ±0.05 V	2.40 ±0.08 V	0 V	0.20 ±0.025 V	Available
S-8243BAHFT-TB-x	4.315 ±0.025 V	–0.20 ±0.05 V	2.00 ±0.08 V	0.15 ±0.10 V	0.20 ±0.025 V	Available

Remark 1. Change in the detection voltage is available in products other than listed above. Contact our sales office.

2. x: G or U

3. Please select products of environmental code = U for Sn 100%, halogen-free products.

Pin Configuration

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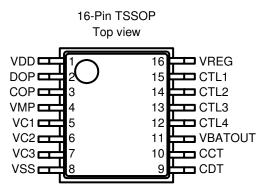


Figure 3

Table 3	Pin descri	ption (S-8243	A Series)
14010 0			

Pin No.	Symbol	Description
1	VDD	Input pin for positive power supply, Connection pin for battery 1's positive voltage
2	DOP	Connection pin for discharge control FET gate (CMOS output)
3	COP	Connection pin for charge control FET gate (Nch open drain output)
4	VMP	Pin for voltage detection between VDD-VMP pin (Pin for overcurrent detection)
5	VC1	No connection
6	VC2	Connection pin for battery 1's negative voltage, for battery 2's positive voltage
7	VC3	Connection pin for battery 2's negative voltage, for battery 3's positive voltage
8	VSS	Input pin for negative power supply, Connection pin for battery 3's negative voltage
9	CDT	Connection pin to capacitor for overdischarge detection delay, for overcurrent detection delay 1
10	CCT	Connection pin to capacitor for overcharge detection delay
11	VBATOUT	Output pin for battery voltage and offset voltage
12	CTL4	Pin for selecting output from VBATOUT pin
13	CTL3	Pin for selecting output from VBATOUT pin
14	CTL2	Control pin for charge / discharge FET
15	CTL1	Control pin for charge / discharge FET
16	VREG	Output pin for voltage regulator (3.3 V)

Table 4 Pin description (S-8243B Series)

Pin No.	Symbol	Description
1	VDD	Input pin for positive power supply, Connection pin for battery 1's positive voltage
2	DOP	Connection pin for discharge control FET gate (CMOS output)
3	COP	Connection pin for charge control FET gate (Nch open drain output)
4	VMP	Pin for voltage detection between VDD-VMP pin (Pin for overcurrent detection)
5	VC1	Connection pin for battery 1's negative voltage, for battery 2's positive voltage
6	VC2	Connection pin for battery 2's negative voltage, for battery 3's positive voltage
7	VC3	Connection pin for battery 3's negative voltage, for battery 4's positive voltage
8	VSS	Input pin for negative power supply, Connection pin for battery 4's negative voltage
9	CDT	Connection pin to capacitor for overdischarge detection delay, for overcurrent detection delay 1
10	ССТ	Connection pin to capacitor for overcharge detection delay
11	VBATOUT	Output pin for battery voltage and offset voltage
12	CTL4	Pin for selecting output from VBATOUT pin
13	CTL3	Pin for selecting output from VBATOUT pin
14	CTL2	Control pin for charge / discharge FET
15	CTL1	Control pin for charge / discharge FET
16	VREG	Output pin for voltage regulator (3.3 V)

Absolute Maximum Ratings

			(Ta = 25°C unless otherwise sp	pecified)
Item	Symbol	Applied Pins	Absolute Maximum Ratings	Unit
Input voltage VDD	V _{DS}	-	V_{SS} –0.3 to V_{SS} +26	V
Input voltage	V _{IN}	VC1, VC2, VC3, CCT, CDT	$V_{SS}0.3$ to $V_{DD}\mbox{+-}0.3$	V
VMP pin Input voltage	V _{MP}	VMP	V_{SS} –0.3 to V_{SS} +26	V
DOP pin output voltage	V _{DOP}	DOP	V_{SS} –0.3 to V_{DD} +0.3	V
COP pin output voltage	V _{COP}	COP	V_{SS} –0.3 to V_{SS} +26	V
VREG pin output voltage	V _{OUT}	VREG	V_{SS} –0.3 to V_{DD} +0.3	V
CTL1 pin input voltage	V _{CTL1}	CTL1	V _{SS} -0.3 to V _{DD} +0.3	V
CTL2 to CTL4 pin input voltage	V _{CTLn}	CTL2, CTL3, CTL4	V_{SS} –0.3 to V_{OUT} +0.3	V
Cell voltage output voltage	VBATOUT	VBATOUT	V_{SS} –0.3 to V_{OUT} +0.3	V
Dower discinction	Р	-	300 (When not mounted on board)	mW
Power dissipation	P _D		1100 ^{*1}	mW
Operation ambient temperature	T _{opr}		-40 to +85	°C
Storage temperature	T _{sta}	_	-40 to +125	°C

Table 5

*1. When mounted on board

[Mounted board]

(1) Board size : 114.3 mm × 76.2 mm × t1.6 mm

(2) Board name : JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

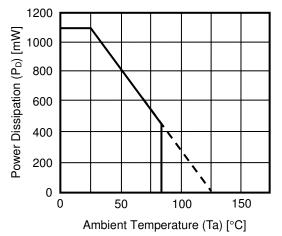


Figure 4 Power Dissipation of Package (When Mounted on Board)

Electrical Characteristics

1. S-8243A Series

		,		(Ta = 25	5°C unless o	otherwise	e specified)
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test circuit
BATTERY PROTECTION						_	-
Overcharge detection voltage n	V _{CUn}	3.9 V to 4.4 V, 50 mV Step	V _{CUn}	V _{CUn}	V _{CUn}	v	4
n=1, 2, 3	V CUn	5.9 V 10 4.4 V, 50 mV Step	-0.025	V CUn	+0.025	v	4
Hysteresis voltage n of overcharge			V _{HCn}		V _{HCn}		
detection	V _{HCn}	-0.10 V to -0.40 V, and 0 V	-0.05	V _{HCn}	+0.05	V	4
n = 1, 2, 3							
Overdischarge detection voltage	V _{DLn}	2.0 V to 3.0 V, 100 mV Step	V _{DLn}	V _{DLn}	V _{DLn}	V	4
n = 1, 2, 3	DEI		-0.08	DEI	+0.08		
Hysteresis voltage n of	V	0.45.1/4= 0.70.1/ ===1.0.1/	V _{HDn}	N	V _{HDn}	N	4
Overdischarge detection	V _{HDn}	0.15 V to 0.70 V, and 0 V	-0.10	V_{HDn}	+0.10	V	4
n = 1, 2, 3			M		V		
Overcurrent detection voltage 1	V _{IOV1}	0.05 V to 0.3 V, 50 mV Step VM voltage based on V _{DD}	V _{IOV1} -0.025	V _{IOV1}	V _{IOV1} +0.025	V	4
Overcurrent detection voltage 2	V	VM voltage based on V_{DD}	0.40	0.50	0.60	V	4
Overcurrent detection voltage 3	V _{IOV2}	VIN VOILAGE DASED ON V _{DD}	0.40 V _{DD} ×0.425			V	4
Temperature coefficient for	V _{IOV3}	_	v _{DD} ×0.420	V _{DD} ×0.5	V _{DD} ×0.575	V	4
detection and release voltage ^{*1}	T _{COE1}	$Ta = -5^{\circ}C \text{ to } +55^{\circ}C^{*3}$	-1.0	0	1.0	mV/°C	4
Temperature coefficient for							
overcurrent detection voltage ^{*2}	T _{COE2}	$Ta = -5^{\circ}C \text{ to } +55^{\circ}C^{*3}$	-0.5	0	0.5	mV/°C	4
0 V BATTERY CHARGING FUNCT	ION (The	I NV hattery function is either "NV hat	I terv charging is	allowed " or "	I '0 V batterv ch:	l araina is ir	hihited "
		nding upon the product type.)	tory onarging io		o v ballory on	arging is in	inibited.
0 V battery charge starting charger							
voltage	V _{OCHA}	0 V battery charging available	-	0.8	1.5	V	7
0 V battery charge inhibition battery							_
voltage	V _{0INH}	0 V battery charging unavailable	0.4	0.7	1.1	V	7
INTERNAL RESISTANCE							
Internal resistance between	р		500	1100	0400	ko	0
VMP and VDD	R _{VDM}	V1 = V2 = V3 = 3.5 V	500	1100	2400	kΩ	8
Internal resistance between	R _{VSM}	V1 = V2 = V3 = 1.8 V	300	700	1500	kΩ	8
VMP and VSS	INVSM	VT = VZ = V3 = 1.0 V	500	700	1500	NS2	0
VOLTAGE REGULATOR	.		i		i	1	
Output voltage	V _{OUT}	V _{DD} = 14 V, I _{OUT} = 3 mA	3.221	3.300	3.379	V	2
Line regulation	ΔV_{OUT1}	V _{DD} = 6 V→18 V, I _{OUT} = 3 mA	-	5	15	mV	2
Load regulation	ΔV_{OUT2}	V_{DD} = 14 V, I_{OUT} = 5 μ A \rightarrow 3 mA	-	15	30	mV	2
BATTERY MONITOR AMP	1		1		1	1	
Input offset voltage n	V _{OFFn}	V1 = V2 = V3 = 3.5 V	60	165	270	mV	3
n = 1, 2, 3	• OFFI			100	2/0		
Voltage gain n	GAMPn	V1 = V2 = V3 = 3.5 V	0.2×0.99	0.2	0.2×1.01	_	3
n = 1, 2, 3							
INPUT VOLTAGE, OPERATING VO	DLTAGE	ł	1		1	1	
Operating voltage between	V _{DSOP}	_	6	-	18	V	4
V _{DD} and V _{SS}							
CTL1 input voltage for High	V _{CTL1H}	-	V _{DD} ×0.8	-	-	V	6
CTL1 input voltage for Low	V _{CTL1L}	_	-	_	V _{DD} ×0.2	V	6
CTLn input voltage for High	V _{CTLnH}	-	V _{OUT} ×0.9	-	V _{OUT}	V	3, 6
n = 2, 3, 4							
CTLn input voltage for Low	V _{CTLnL}	-	-	-	V _{OUT} ×0.1	V	3, 6
n = 2, 3, 4							

Table 6 (1 / 2)

BATTERY PROTECTION IC FOR 3-SERIAL OR 4-SERIAL CELL PACK S-8243A/B Series

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Item	Symbol	Remarks	Min.	Тур.	Max.	Unit	Test circuit
INPUT CURRENT	-		_	-	-		
Current consumption at not monitoring V _{BATOUT}	I _{OPE}	$V1 = V2 = V3 = 3.5 V, V_{MP} = V_{DD}$	-	65	120	μA	1
Current consumption at power down	I _{PDN}	$V1 = V2 = V3 = 1.5 V, V_{MP} = V_{SS}$	-	-	0.1	μA	1
Current for VCn at not monitoring V _{BATOUT} (n = 2, 3)	I _{VCnN}	V1 = V2 = V3 = 3.5 V	-0.3	0	0.3	μA	3
Current for VC2 at monitoring of V _{BATOUT}	I _{VC2}	V1 = V2 = V3 = 3.5 V	-	2.0	7.2	μA	3
Current for VC3 at monitoring of V_{BATOUT}	I _{VC3}	V1 = V2 = V3 = 3.5 V	-	1.0	4.0	μA	3
Current for CTL1 at Low	I _{CTL1L}	V1 = V2 = V3 = 3.5 V, V _{CTL1} = 0 V	-0.4	-0.2	-	μA	5
Current for CTLn at High n = 2,3,4	I _{CTLnH}	$V_{CTLn} = V_{OUT}$	-	2.5	5	μA	9
Current for CTLn at Low n = 2,3,4	I _{CTLnL}	V _{CTLn} = 0 V	-5	-2.5	-	μA	9
OUTPUT CURRENT							
Leak current COP	I _{COH}	$V_{COP} = 24 V$	-	-	0.1	μA	9
Sink current COP	I _{COL}	$V_{COP} = V_{SS} + 0.5 V$	10	-	-	μA	9
Source current DOP	I _{DOH}	$V_{DOP} = V_{DD} - 0.5 V$	10	-	_	μA	9
Sink current DOP	I _{DOL}	$V_{DOP} = V_{SS} + 0.5 V$	10	-	_	μA	9
Source current V _{BATOUT}	I _{VBATH}	$V_{BATOUT} = V_{DD} - 0.5 V$	100	-	_	μA	9
Sink current V _{BATOUT}	I _{VBATL}	$V_{BATOUT} = V_{SS} + 0.5 V$	100	-	-	μA	9

Table 6 (2 / 2)

Applied to S-8243AACFT and S-8243AADFT

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test circuit
DELAY TIME							
Overcharge detection delay time	t _{cu}	$C_{CT} = 0.1 \ \mu F$	0.5	1.0	1.5	S	5
Overdischarge detection delay time	t _{DL}	$C_{DT} = 0.1 \ \mu F$	50	100	150	ms	5
Overcurrent detection delay time 1	t _{IOV1}	$C_{DT} = 0.1 \ \mu F$	5	10	15	ms	5
Overcurrent detection delay time 2	t _{IOV2}	_	1.5	2.5	4.0	ms	4
Overcurrent detection delay time 3	t _{IOV3}	_	100	300	600	μS	4

*1. Temperature coefficient for detection and release voltage is applied to overcharge detection voltage n, overcharge release voltage n, overdischarge detection voltage n, and overdischarge release voltage n.

*2. Temperature coefficient for overcurrent detection voltage is applied to over current detection voltage 1 and 2.

*3. Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.

2. S-8243B Series

			-	(Ta = 2	5°C unless o	otherwis	e specified
Item	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test circuit
DETECTION VOLTAGE							
Overcharge detection voltage n	V _{CUn}	3.9 V to 4.4 V, 50 mV Step	V _{CUn}	V _{Cun}	V _{CUn}	V	4
n = 1, 2, 3, 4	V CUn	5.9 V to 4.4 V, 50 mV Step	-0.025		+0.025	v	4
Hysteresis voltage n of overcharge			V _{HCn}		V _{HCn}		
detection	V _{HCn}	–0.10 V to –0.40 V, and 0 V	-0.05	V _{HCn}	+0.05	V	4
n = 1, 2, 3, 4							
Overdischarge detection voltage	V _{DLn}	2.0 V to 3.0 V, 100 mV Step	V _{DLn} -0.08	V _{DLn}	V _{DLn}	V	4
n = 1, 2, 3, 4 Hysteresis voltage n of			-0.00		+0.08		
overdischarge detection	V _{HDn}	0.15 V to 0.70 V, and 0 V	V_{HDn}	V _{HDn}	V _{HDn}	V	4
n = 1, 2, 3, 4	♥ HDn	0.15 V 10 0.70 V, and 0 V	-0.10	♥ HDn	+0.10	v	т
		0.05 V to 0.3 V, 50 mV Step	V _{IOV1}		V _{IOV1}		
Overcurrent detection voltage 1	V _{IOV1}	VM voltage based on V _{DD}	-0.025	V _{IOV1}	+0.025	V	4
Overcurrent detection voltage 2	V _{IOV2}	VM voltage based on V _{DD}	0.40	0.50	0.60	V	4
			V _{DD}	V _{DD}	V _{DD}	V	
Overcurrent detection voltage 3	V _{IOV3}	-	×0.425	×0.5	×0.575	V	4
Temperature coefficient for detection and release voltage ^{*1}	T _{COE1}	$Ta = -5^{\circ}C \text{ to } +55^{\circ}C^{*3}$	-1.0	0	1.0	mV/°C	4
Temperature coefficient for		*0					
overcurrent detection voltage ^{*2}	T _{COE2}	$Ta = -5^{\circ}C \text{ to } +55^{\circ}C^{*3}$	-0.5	0	0.5	mV/°C	4
0 V BATTERY CHARGING FUNC	TION (The	e 0 V battery function is either "0 V	battery chargir	ng is allowed.	or "0 V batte	ry chargin	a is inhibited
		pending upon the product type.)	, ,	0		, ,	0
0 V battery charge starting charger							_
voltage	V _{OCHA}	0 V battery charging allowed	-	0.8	1.5	V	7
0 V battery charge inhibition battery	V _{0INH}	0 V battery charging inhibited	0.4	0.7	1.1	v	7
voltage	♥ 0INH	o v ballery charging innibiled	0.4	0.7	1.1	v	I
INTERNAL RESISTANCE		Ι		1	1	-	1
Internal resistance between VMP and VDD	R _{VDM}	V1 = V2 = V3 = V4 = 3.5 V	500	1100	2400	kΩ	8
Internal resistance between	_			700	4500		
VMP and VSS	R _{VSM}	V1 = V2 = V3 = V4 = 1.8 V	300	700	1500	kΩ	8
VOLTAGE REGULATOR							
Output voltage	V _{OUT}	V _{DD} = 14V, I _{OUT} = 3 mA	3.221	3.300	3.379	V	2
Line regulation	ΔV_{OUT1}	$V_{DD} = 6 \text{ V} \rightarrow 18 \text{ V}, I_{OUT} = 3 \text{ mA}$	-	5	15	mV	2
Load regulation	ΔV_{OUT2}	V_{DD} = 14 V, I_{OUT} = 5 μ A \rightarrow 3 mA	-	15	30	mV	2
BATTERY MONITOR AMP						_	
Input offset voltage n	V _{OFFn}	V1 = V2 = V3 = V4 = 3.5 V	60	165	270	mV	3
n = 1, 2, 3, 4	V OFFn	$v_1 = v_2 = v_3 = v_4 = 3.5 v_1$	00	105	270	IIIV	3
Voltage gain n	GAMPn	V1 = V2 = V3 = V4 = 3.5 V	0.2×0.99	0.2	0.2×1.01	_	3
n = 1, 2, 3, 4		VI = VL = VO = VH = 0.0 V	0.2×0.00	0.2	0.2~1.01		0
INPUT VOLTAGE, OPERATING VO	OLTAGE	Γ			1		1
Operating voltage between	VDSOP	-	6	_	18	v	4
V _{DD} and V _{SS}						-	
CTL1 input voltage for High	V _{CTL1H}	-	V _{DD} ×0.8	-	-	V	6
CTL1 input voltage for Low	V _{CTL1L}	-	-	-	V _{DD} ×0.2	V	6
CTLn input voltage for High	V _{CTLnH}	-	V _{OUT} ×0.9	_	V _{OUT}	v	3, 6
n = 2, 3, 4			001-000				, -
CTLn input voltage for Low	V _{CTLnL}	-	-	-	V _{OUT} ×0.1	V	3, 6
n = 2, 3, 4		1					

BATTERY PROTECTION IC FOR 3-SERIAL OR 4-SERIAL CELL PACK S-8243A/B Series

Rev.3.0_00

Item	Symbol	Remarks	Min.	Тур.	Max.	Unit	Test circuit		
INPUT CURRENT									
Current consumption at not monitoring V _{BATOUT}	I _{OPE}	$V1 = V2 = V3 = V4 = 3.5 V, V_{MP} = V_{DD}$	-	65	120	μA	1		
Current consumption at power down	I _{PDN}	$V1 = V2 = V3 = V4 = 1.5 V$, $V_{MP} = V_{SS}$	-	-	0.1	μA	1		
Current for VCn at not monitoring V _{BATOUT} (n = 2, 3)	I _{VCnN}	V1 = V2 = V3 = V4 = 3.5 V	-0.3	0	0.3	μA	3		
Current for VC1 at monitoring of V _{BATOUT}	I _{VC1}	V1 = V2 = V3 = V4 = 3.5 V	-	3.2	10.4	μA	3		
Current for VC2 at monitoring of V _{BATOUT}	I _{VC2}	V1 = V2 = V3 = V4 = 3.5 V	-	2.0	7.2	μA	3		
Current for VC3 at monitoring of V_{BATOUT}	I _{VC3}	V1 = V2 = V3 = V4 = 3.5 V, V _{CTL1} = 0 V	-	1.0	4.0	μA	3		
Current for CTL1 at Low	I _{CTL1L}	$V1 = V2 = V3 = V4 = 3.5 V, V_{CTL1} = 0 V$	-0.4	-0.2	1	μA	5		
Current for CTLn at High n = 2, 3, 4	I _{CTLnH}	V _{CTLn} = V _{OUT}	-	2.5	5	μA	9		
Current for CTLn at Low n = 2, 3, 4	I _{CTLnL}	V _{CTLn} = 0 V	-5	-2.5	-	μA	9		
OUTPUT CURRENT									
Leak current COP	I _{COH}	$V_{COP} = 24 V$	-	-	0.1	μA	9		
Sink current COP	I _{COL}	$V_{COP} = V_{SS} + 0.5 V$	10	_	-	μA	9		
Source current DOP	I _{DOH}	$V_{DOP} = V_{DD} - 0.5 V$	10	-	-	μA	9		
Sink current DOP	IDOL	$V_{DOP} = V_{SS} + 0.5 V$	10	-	-	μA	9		
Source current V _{BATOUT}	I _{VBATH}	$V_{BATOUT} = V_{DD} - 0.5 V$	100	-	-	μA	9		
Sink current V _{BATOUT}	I _{VBATL}	$V_{BATOUT} = V_{SS} + 0.5 V$	100	_	-	μA	9		

Table 7 (2 / 2)

Applied to S-8243BAEFT, S-8243BAFFT, S-8243BAHFT

ltem	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test circuit		
DELAY TIME									
Overcharge detection delay time	t _{cu}	C _{CT} = 0.1 μF	0.5	1.0	1.5	s	5		
Overdischarge detection delay time	t _{DL}	$C_{DT} = 0.1 \ \mu F$	50	100	150	ms	5		
Overcurrent detection delay time 1	t _{IOV1}	$C_{DT} = 0.1 \ \mu F$	5	10	15	ms	5		
Overcurrent detection delay time 2	t _{IOV2}	_	1.5	2.5	4.0	ms	4		
Overcurrent detection delay time 3	t _{IOV3}	_	100	300	600	μS	4		

Applied to S-8243BADFT

ltem	Symbol	Conditions	Min.	Тур.	Max.	Unit	Test circuit		
DELAY TIME									
Overcharge detection delay time	t _{cu}	$C_{CT} = 0.1 \ \mu F$	0.5	1.0	1.5	S	5		
Overdischarge detection delay time	t _{DL}	$C_{DT} = 0.1 \ \mu F$	55.5	111	222	ms	5		
Overcurrent detection delay time 1	t _{IOV1}	$C_{DT} = 0.1 \ \mu F$	3.31	6.62	13.2	ms	5		
Overcurrent detection delay time 2	t _{IOV2}	_	1.5	2.5	4.0	ms	4		
Overcurrent detection delay time 3	t _{IOV3}	-	100	300	600	μS	4		

*1. Temperature coefficient for detection and release voltage is applied to overcharge detection voltage n, overcharge release voltage n, overdischarge detection voltage n, and overdischarge release voltage n.

*2. Temperature coefficient for overcurrent detection voltage is applied to over current detection voltage 1 and 2.

*3. Since products are not screened at high and low temperature, the specification for this temperature range is guaranteed by design, not tested in production.

Test Circuits

In this chapter test methods are explained for the case of S-8243B series, which is designed for 4-serial cell pack. For the case of S-8243A series, which is designed for 3-serial cell, voltage source V2 should be shorted, V3 should be read as V2, and V4 as V3.

1. Current consumption (Test circuit 1)

Current consumption at not monitoring V_{BATOUT} , I_{OPE} , is a current measured at the VSS pin when V1 = V2 = V3 = V4 = 3.5 V and $V_{MP} = V_{DD}$. Current consumption at power down, I_{PDN} , is a current measured at the VSS pin when V1 = V2 = V3 = V4 = 1.5 V and $V_{MP} = V_{SS}$.

2. Voltage regulator (Test circuit 2)

Output voltage of the regulator V_{OUT} is a voltage measured at the VREG pin when $V_{DD} = V_{MP} = 14$ V and $I_{OUT} = 3$ mA. Line regulation of the voltage regulator ΔV_{OUT1} is defined by the equation $\Delta V_{OUT1} = V_{OUT2} - V_{OUT1}$ where V_{OUT1} is the output voltage when $V_{DD} = V_{MP} = 6$ V and $I_{OUT} = 3$ mA, and V_{OUT2} is the output voltage when $V_{DD} = V_{MP} = 18$ V and $I_{OUT} = 3$ mA.

Load regulation of the regulator is defined by the equation $\Delta V_{OUT2} = V_{OUT3} - V_{OUT}$ where V_{OUT3} is the output voltage when $V_{DD} = V_{MP} = 14$ V and $I_{OUT} = 5$ µA.

3. Battery monitor amp and pin current for VC1 to VC3 (Test circuit 3)

Voltage gain of the battery monitor amp for each cell is defined by the input offset voltage and the measurement result provided from the VBATOUT pin for the combination of the CTL3 pin and CTL4 pin expressed by the following table at the condition where V1 = V2 = V3 = V4 = 3.5 V. Pin current for VC1 to VC3, I_{VCn} and I_{VCnN} are at the same time measured.

CTL3 pin status	CTL4 pin status	VBATOUT pin output	VCn (n = 1, 2, 3) pin current
V _{CTL3H} min.	V _{CTL4H} min.	V _{OFF1}	I _{VC1} at VC1 pin
V _{CTL3H} min.	Open	V _{BAT1}	_
V _{CTL3H} min.	V _{CTL4L} max.	V _{OFF2}	I _{VC2} at VC2 pin
Open	V _{CTL4H} min.	V _{BAT2}	_
Open	Open	V _{OFF3}	I _{VC3} at VC3 pin
Open	V _{CTL4L} max.	V _{BAT3}	_
V _{CTL3L} max.	V _{CTL4H} min.	V _{OFF4}	I_{VCnN} at VCn pin (n = 1, 2, 3)
V _{CTL3L} max.	Open	V_{BAT4}	_

Table 8

Voltage gain of the battery monitor amp for each cell is calculated by the equation $GAMPn = (V_{BATn} - V_{OFFn}) / Vn (n = 1 to 4)$

4. Overcharge detection voltages, overcharge detection hysteresis, overdischarge detection voltages, overdischarge detection hysteresis, and overcurrent detection voltages (Test circuit 4)

4.1 Overcharge detection voltages, hysteresis voltages, and overdischarge detection voltages

In the following $V_{MP} = V_{DD}$ and the CDT pin is open.

The COP pin and the DOP pin should provide "Low", which is a voltage equal to $V_{DD} \times 0.1$ V or lower, in the condition that V1 = V2 = V3 = V4 = 3.5 V.

The overcharge detection voltage V_{CU1} is defined by the voltage at which COP pin voltage becomes "High", which is a voltage equal to VDD × 0.9 V or higher, when the voltage V1 is gradually increased from the starting condition V1 = 3.5 V. The overcharge release voltage V_{CL1} is defined by the voltage at which COP pin voltage becomes "Low" when the voltage V1 is gradually decreased. The hysteresis voltage of the overcharge detection V_{HC1} is then defined by the difference between the overcharge detection voltage V_{CU1} and the overcharge release voltage V_{CL1} .

The overdischarge detection voltage V_{DL1} is defined by the voltage at which DOP pin voltage becomes "High" when the voltage V1 is gradually decreased from the starting condition V1 = 3.5 V. The overdischarge release voltage V_{DU1} is defined by the voltage at which DOP pin voltage becomes "Low" when the voltage V1 is gradually increased. The hysteresis of the overdischarge detection voltage V_{HD1} is then defined by the difference between the overdischarge release voltage V_{DU1} and the overdischarge detection voltage V_{DL1} .

Other overcharge detection voltage V_{CUn} , hysteresis voltage of overcharge detection V_{HCn} , overdischarge detection voltage V_{DLn} , and hysteresis of the overdischarge detection voltage V_{HDn} (for n = 2 to 4) are defined in the same manner as in the case for n = 1.

4. 2 Overcurrent detection voltages

Starting condition is V1 = V2 = V3 = V4 = 3.5 V, VMP = VDD, and the CDT pin is open. The DOP pin voltage thus provides "Low"

The overcurrent detection voltage 1, VIOV1 is defined by the voltage difference VDD – VMP at which the DOP pin voltage becomes "High" when the voltage of VMP pin is decreased.

Starting condition for measuring the overcurrent detection voltage 2 and 3 is V1 = V2 = V3 = V4 = 3.5 V, $V_{MP} = V_{DD}$ and the CDT pin voltage $V_{CDT} = V_{SS}$. The DOP pin voltage thus provides "Low".

The overcurrent detection voltage 2, V_{IOV2} is defined by the voltage difference $V_{DD}-V_{MP}$ at which the DOP pin voltage becomes "High" when the voltage of VMP pin is decreased.

The overcurrent detection delay time 2, t_{IOV2} is a time needed for the DOP pin to become "High" from "Low" when the VM pin voltage is changed quickly to V_{IOV2} min.-0.2 V from the starting condition $V_{MP} = V_{DD}$.

The overcurrent detection voltage 3, V_{IOV3} is defined by the voltage of the VM pin at which the DOP pin voltage becomes "High" when the voltage of VMP pin is decreased at the speed 10 V / ms.

The overcurrent detection delay time 3, t_{IOV3} is a time needed for the DOP pin to become "High" from "Low" when the VM pin voltage is changed quickly to V_{IOV3} min.-0.2 V from the starting condition $V_{MP} = V_{DD}$.

5. CTL1 pin current, overcharge detection delay, overdischarge detection delay, and overcurrent detection delay 1 (Test circuit 5)

Starting condition is V1 = V2 = V3 = V4 = 3.5 V and V_{MP} = V_{DD}. Current that flows between the CTL1 pin and V_{SS} is the CTL1 pin current I_{CTL1L}.

The overcharge detection delay time t_{CU} is a time needed for the COP pin voltage to change from "Low" to "High" just after the V1 voltage is rapidly increased from 3.5 V to 4.5 V.

The overdischarge detection delay time t_{DL} is a time needed for the DOP pin voltage to change from "Low" to "High" just after the V1 voltage is rapidly decreased from 3.5 V to 1.5 V.

The overcurrent detection delay time 1 is a time needed for the DOP pin voltage to change from "Low" to "High" just after the VMP pin voltage is decreased from V_{DD} to V_{DD} -0.35 V when V1 = 3.5 V.

6. Input voltages for CTL1 and CTL2 (Test circuit 6)

Starting condition is V1 = V2 = V3 = V4 = 3.5 V.

Pin voltages of the COP and the DOP should be "High" when $V_{CTL1} = V_{CTL1H}$ min. and CTL2 is OPEN.

Pin voltages of the COP and the DOP should be "Low" when $V_{CTL1} = V_{CTL1L}$ max. and CTL2 is OPEN.

Pin voltage of the COP is "High" and the pin voltage of the DOP is "Low" when $V_{CTL1} = V_{CTL1L}$ max. and $V_{CTL2} = V_{CTL2H}$ min.

Pin voltage of the COP is "Low" and the pin voltage of the DOP is "High" when $V_{CTL1} = V_{CTL1L}$ max. and $V_{CTL2} = V_{CTL2L}$ max.

7. 0 V battery charge starting charger voltage and 0 V battery charge inhibition battery voltage (Test circuit 7)

One of the 0 V battery charge starting charger voltage and 0 V battery charge inhibition battery voltage is applied to each product according to the 0V battery charging function.

Starting condition is V1 = V2 = V3 = V4 = 0 V for a product in which 0 V battery charging is available. The COP pin voltage should be lower than V_{0CHA} max.-1 V when the VMP pin voltage $V_{MP} = V_{0CHA}$ max.

Starting condition is V1 = V2 = V3 = V4 = V_{0INH} for a product in which 0 V battery charging is inhibited. The COP pin voltage should be higher than V_{MP} -1 V when the VMP pin voltage V_{MP} = 24 V.

8. Internal resistance (Test circuit 8)

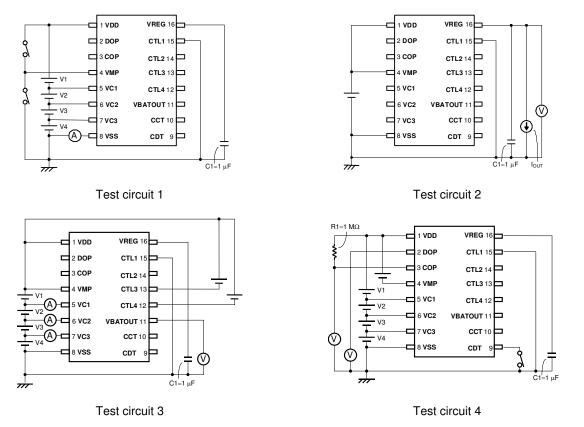
The resistance between VDD and VMP is R_{VDM} and is calculated by the equation $R_{VDM} = V_{DD} / I_{VDM}$ where I_{VDM} is a VMP pin current after V_{MP} is changed to V_{SS} from the starting condition V1 = V2 = V3 = V4 = 3.5 V and $V_{MP} = V_{DD}$. The resistance between VSS and VMP is R_{VSM} and is calculated by the equation $R_{VSM} = V_{DD} / I_{VSM}$ where I_{VSM} is a VMP pin current at the condition V1 = V2 = V3 = V4 = 1.8 V and $V_{MP} = V_{DD}$.

9. Pin current for CTL2 to CTL4, COP, DOP, VBATOUT (Test circuit 9)

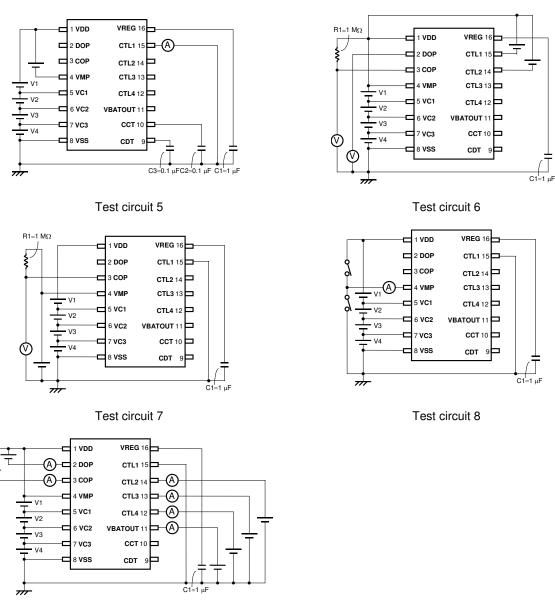
Starting condition is V1 = V2 = V3 = V4 = 3.5 V. Pin current for CTL2 at "High" is I_{CTL2H} and is obtained by setting $V_{CTL2} = V_{OUT}$. Pin current for CTL2 at "Low" is I_{CTL2L} and is obtained by setting $V_{CTL2} = V_{SS}$. Pin current for CTL3 and CTL4 can be obtained in the same manner as in the CTL2.

Pin current for COP at "High" is I_{COH} and is obtained by setting V1 = V2 = V3 = V4 = 6 V, V_{MP} = V_{DD}, and V_{COP} = V_{DD}. And pin current for COP at "Low" is I_{COL} and is obtained by setting V1 = V2 = V3 = V4 = 3.5 V, V_{MP} = V_{DD}, and V_{COP} = 0.5 V. Pin current for DOP at "Low" is I_{DOL} and is obtained by setting V1 = V2 = V3 = V4 = 3.5 V, V_{MP} = V_{DD}, and V_{DOP} = 0.5 V. And pin current for COP at "High" is I_{COH} and is obtained by setting V1 = V2 = V3 = V4 = 3.5 V, V_{MP} = V_{DD}, and V_{DOP} = 0.5 V. And pin current for COP at "High" is I_{COH} and is obtained by setting V1 = V2 = V3 = V4 = 3.5 V, V_{MP} = V_{DD}-1 V, and V_{DOP} = V_{DD}-0.5 V.

Pin current for VBATOUT at "High" is I_{VBATH} and is obtained by setting CTL3 and CTL4 are open and $V_{BATOUT} = V_{OFF3}-0.5 \text{ V}$. And pin current for VBATOUT at "Low" is I_{VBATL} and is obtained by setting $V_{BATOUT} = V_{OFF3}+0.5 \text{ V}$.







Test circuit 9

Figure 5 (2 / 2)

Operation

1. Battery protection circuit

Remark Refer to " Battery Protection IC Connection Example".

Battery protection protects batteries from overcharge and overdischarge, and also protects external FETs from overcurrent.

1.1 Normal status

When all of the battery voltages are in the range from V_{DLn} to V_{CUn} and the discharge current is lower than a specified value (the VMP pin voltage is lower than V_{IOV1}), the charging and discharging FETs are turned on.

1.2 Overcharge status

When any one of the battery voltages becomes higher than V_{CUn} and the state continues for t_{CU} or longer, the COP pin becomes high impedance and is pulled up to EB+ pin voltage by an external resistor, and the charging FET is turned off to stop charging. The overcharge status is released when one of the following two conditions holds.

- (a) All battery voltages become lower than $V_{\text{CUn}} + V_{\text{HCn}}.$
- (b) $V_{DD}-V_{MP}>V_{IOV1}$ (A load is connected, and discharging starts.)

1.3 Overdischarge status

When any one of the battery voltages becomes lower than V_{DLn} and the state continues for t_{DL} or longer, the DOP pin voltage becomes V_{DD} level, and the discharging FET is turned off to stop discharging. This is the overdischarge status.

1.4 Power down status

After stopping discharging due to overdischarge status, the S-8243 enters power down status. In this status, almost all circuits of the S-8243 are stopped to save current consumption. The current consumption becomes lower than I_{PDN} . In the power down status, the VMP pin is pulled down to V_{SS} level by the internal R_{VSM} resistor. In power down status, output pin voltages are fixed at the following levels.

(a) COP	High-Z	(Charging FET is turned off)	
---------	--------	------------------------------	--

- (b) DOP V_{DD} (Discharging FET is turned off)
- (c) VREG V_{SS} (Voltage regulator circuit is off)

(d) VBATOUT V_{SS} (Battery voltage monitor amp circuit is off)

The power down status is released when the following condition holds.

(a) V_{MP} > V_{IOV3} (A charger is connected, and charging starts.)

The overdischarging status is released when the following condition holds.

(a) All of the battery voltages are V_{DLn} or higher, and the VMP pin voltage is VDD / 2 or higher. (A charger is connected.)

1.5 Overcurrent status

The S-8243 has three overcurrent detection levels (V_{IOV1} , V_{IOV2} and V_{IOV3}) and three overcurrent detection delay times (t_{IOV1} , t_{IOV2} and t_{IOV3}) corresponding to each overcurrent detection levels. When the discharging current becomes higher than a specified value (the voltage between V_{DD} and V_{MP} is greater than V_{IOV1}) and the state continues for t_{IOV1} or longer, the S-8243 enters the overcurrent status in which the DOP pin voltage becomes V_{DD} level to turn off the discharging FET to stop discharging, the COP pin becomes high impedance and is pulled up to EB+ pin voltage by an external resistor to turn off the charging FET to stop charging, and the VMP pin is pulled up to V_{DD} voltage by the internal resistor R_{VDM} . Operation of two other overcurrent detection levels (V_{IOV2} and V_{IOV3}) and overcurrent detection delay times (t_{IOV2} and t_{IOV3}) is the same as that for V_{IOV1} and t_{IOV1} .

The overcurrent status is released when the following condition holds.

(a) $V_{MP} > \{V_{IOV3} / (1 - V_{IOV3}) \times 3 / 5 - 2 / 5\} \times R_{VDM}$ (A load is released, and the impedance between the EB- and EB+ pin becomes higher.)

1.6 0 V battery charging function

guaranteed.

Regarding the charging of a self-discharged battery (0 V battery) the S-8243 has two functions from which one should be selected.

- (a) 0 V battery charging is allowed (0 V battery charging is available)
 When a charger voltage is higher than V_{0CHA}, 0 V battery can be charged.
- (b) 0 V battery charging is forbidden (0 V battery charging is impossible)
 When one of the battery voltages is lower than V_{0INH}, 0 V battery can not be charged.

Caution When the VDD pin voltage is lower than minimum of V_{DSOP}, the operation of S-8243 series is not

1.7 Delay time setting

Overcharge detection delay times (t_{CU1} to t_{CU4}) are determined by the external capacitor at the CCT pin. Overdischarge detection delay times (t_{DL1} to t_{DL4}) and overcurrent detection delay time 1 (t_{IOV1}) are determined by the external capacitor at CDT pin. Overcurrent detection delay time 2,3 (t_{IOV2} , t_{IOV3}) are fixed internally.

S-8243AAC, S-8243AAD, S-8243BAE, S-8243BAF, S-8243BAH

		min.	typ.	max.	
t _{CU} [s]	= Delay factor (5	10	15	$) \times C_{CT} [\mu F]$
t _{DL} [ms]	= Delay factor (500	1000	1500	$) \times C_{\text{DT}} [\mu F]$
t _{IOV1} [ms]	= Delay factor (50	100	150	$) \times C_{\text{DT}} [\mu F]$

S-8243BAD

		min.	typ.	max.	
t _{CU} [s]	= Delay factor (5	10	15	$) \times C_{CT} [\mu F]$
t _{DL} [ms]	= Delay factor (555	1110	2220	$) \times C_{\text{DT}} \left[\mu F \right]$
t _{IOV1} [ms]	= Delay factor (33.1	66.2	132	$) \times C_{DT} [\mu F]$

2. Voltage regulator circuit

Built-in voltage regulator can be used to drive a micro computer, etc. The voltage regulator supplies voltage of 3.3 V (3 mA maximum) and an external capacitor is needed.

Caution In the power down status the voltage regulator output is pulled down to the V_{SS} level by an internal resistor.

3. Battery monitor amp circuit

Battery monitor amp sends information of the batteries to a microcomputer. The battery monitor amp output is controlled and selected by CTL3 and CTL4 pins to give the following two voltages.

- (a) $V_{BATn} = GAMPn \times V_{BATTERYn} + V_{OFFn}$ where GAMPn is the n-th voltage gain of the amp, $V_{BATTERYn}$ is the n-th battery voltage, and V_{OFFn} is the n-th offset voltage of the amp.
- (b) N-th offset voltage V_{OFFn}

Each battery voltage $V_{BATTERYn}$ (n = 1 to 4) is thus calculated by following equation. $V_{BATTERYn} = (V_{BATn} - V_{OFFn}) / GAMPn$ (n = 1, 2, 3, 4)

After the state of CTL3 and CTL4 are changed, a time between 25 μ s and 250 μ s is needed for the battery monitor amp to become stable.

Caution In the power down status the battery monitor amp output is the V_{SS} level.

4. CTL pins

The S-8243 has four control pins. The CTL1 and CTL2 pins are used to control the COP and DOP pin output voltages. CTL1 takes precedence over CTL2. CTL2 takes precedence over the battery protection circuit. The CTL3 and CTL4 pins are used to control the VBATOUT pin output voltage.

Inp	out	Output		
CTL1 pin	CTL2 pin	External discharging FET	External charging FET	
High	High	OFF	OFF	
High	Open	OFF	OFF	
High	Low	OFF	OFF	
Open	High	OFF	OFF	
Open	Open	OFF	OFF	
Open	Low	OFF	OFF	
Low	High	Normal ^{*1}	OFF ^{*2}	
Low	Open	Normal ^{*1}	Normal ^{*1}	
Low	Low	OFF	Normal ^{*1}	

Table 9 CTL1 and CTL2 Mode

*1. States are controlled by voltage detection circuit.

*2. Off state is brought after the overcharge detection delay time t_{CU} .

In	put	Outp	put		
CTL3 pin	CTL4 pin	V _{BATOUT} (A series)	V _{BATOUT} (B series)		
High	High	V1 Offset	V1 Offset		
High	Open	$V1 \times 0.2 + V1$ Offset	$V1 \times 0.2 + V1$ Offset		
High	Low	Don't use.	V2 Offset		
Open	High	Don't use.	$V2 \times 0.2 + V2$ Offset		
Open ^{*1}	Open ^{*1}	V2 Offset	V3 Offset		
Open	Low	$V2 \times 0.2 + V2$ Offset	$V3 \times 0.2 + V3$ Offset		
Low	High	V3 Offset	V4 Offset		
Low	Open	$V3 \times 0.2 + V3$ Offset	$V4 \times 0.2 + V4$ Offset		
Low	Low	Don't use.	Don't use.		

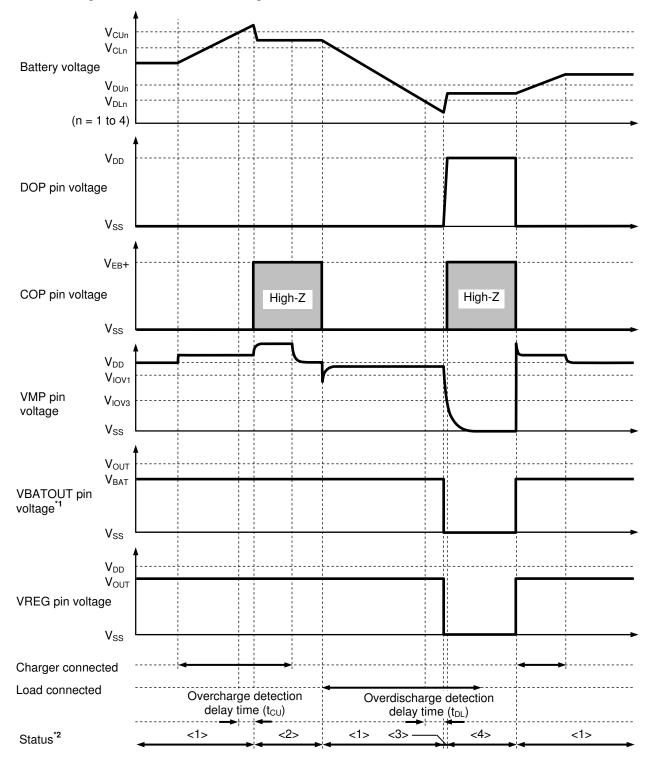
Table 10 CTL3 and CTL4 Mode

*1. CTL3 and CTL4 pins should be open when a microcomputer is not used.

Caution Please note unexpected behavior might occur when electrical potential difference between the CTL pin ("L" level) aMSS is generated through the external filter (R_{VSS} and C_{VSS}) as a result of input voltage fluctuations.

Timing Charts

1. Overcharge detection, Over discharge detection



*1. State depends on CTL3 and CTL4 input levels. Refer to Figure 9.

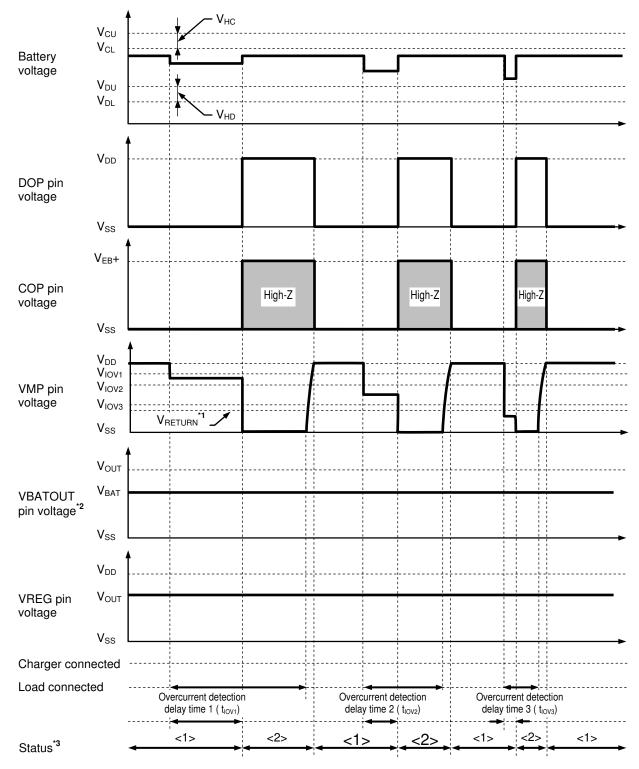
*2. <1>: Normal status, <2>: Overcharge status, <3>: Overdischarge status, <4>: Power down status

Remark The charger is assumed to charge with a constant current. V_{EB+} indicates the open voltage of the charger.

BATTERY PROTECTION IC FOR 3-SERIAL OR 4-SERIAL CELL PACK S-8243A/B Series

Rev.3.0_00

2. Overcurrent detection



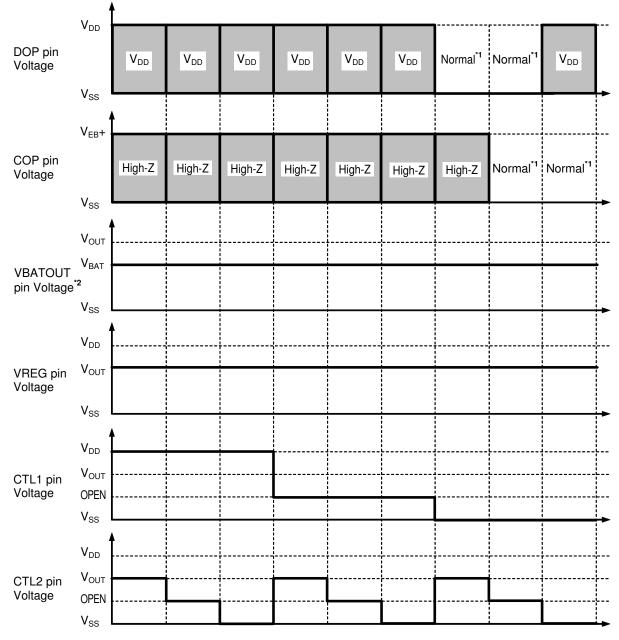
*1. $V_{RETURN} = V_{DD} / 6$ (typ.)

*2. State depends on CTL3 and CTL4 input levels. Refer to Figure 9.

*3. <1>: Normal status, <2>: Overcurrent status

Remark The charger is assumed to charge with a constant current. V_{EB}+ indicates the open voltage of the charger.

3. CTL1, CTL2 pin voltage



*1. State depends on each battery voltage and the VMP pin voltage.

*2. State depends on CTL3 and CTL4 input levels. Refer to Figure 9.

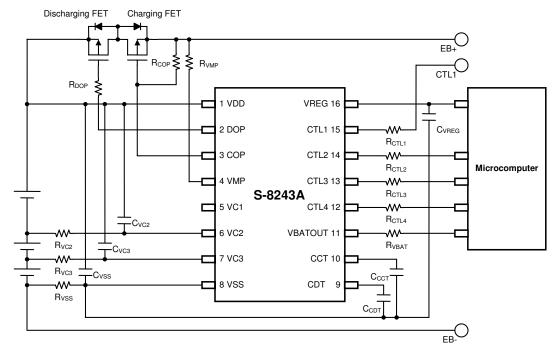
4. CTL3, TL4 pin voltage

		L								
	V _{DD}]							
DOP pin voltage ^{*1}		(1)	(1)	(1)	(1)	(1)	(1)	(1)	(1)	(1)
Ũ	V_{SS}									
	V _{EB} +	t								
COP pin voltage ^{*1}	▼ EB+	(1)	(1)	(1)	(1)	(1)	(1)	(1)	(1)	(1)
voltage	V_{SS}	(1)	(1)	(1)	(1)	(1)	(1)	(1)	(1)	(1)
	1	•								
S-8243A	V _{OUT}		+				+			
(3-serial cell) VBATOUT	V _{BAT} . V _{OFF}		V1 × 0.2	Don't	Don't		V2 × 0.2	 	V3 × 0.2	Don't
pin voltage	V _{SS}	V1 offset	+V1 offset	use	use	V2 offset	+V2 offset	V3 offset	+V3 offset	use
	V _{OUT}	t								
S-8243B (4-serial cell)	V _{BAT}									
VBATOUT pin voltage	V _{OFF}		V1 × 0.2		V2 imes 0.2		V3 imes 0.2		V4 imes 0.2	Don't
pin tonago	V_{SS}	V1 offset	+V1 offset	V2 offset	+V2 offset	V3 offset	+V3 offset	V4 offset	+V4 offset	use
	V _{DD}									
VREG pin voltage	V_{OUT}			1 						
vonage	V_{SS}									
	V _{DD}	t								
	V _{OUT}		 	 						
o i Lo pini	OPEN				<u> </u>					
	V _{SS}									>
	V _{DD}	.								
CTL4 pin	V _{OUT}		.					 	•	
voltage	OPEN		ļ		 	ļ	.		-	
	V_{SS}									▶

*1. State depends on CTL1 and CTL2 and each battery voltage and the VMP pin voltage. Refer to Figure 6 to 8.

Battery Protection IC Connection Example

1. S-8243A Series





No.	Part	Тур.	Range	Unit
1	R _{VC2}	1	0.51 to 1 ^{*1}	kΩ
2	R _{VC3}	1	0.51 to 1 ^{*1}	kΩ
3	R _{vss}	10	2.2 to 10 ^{*1}	Ω
4	R _{DOP}	5.1	2 to 10	kΩ
5	R _{COP}	1	0.1 to 1	MΩ
6	R _{VMP}	5.1	1 to 10	kΩ
7	R _{CTL1}	1	1 to 100	kΩ
8	R _{CTL2}	1	1 to 10	kΩ
9	R _{CTL3}	1	1 to 10	kΩ
10	R _{CTL4}	1	1 to 10	kΩ
11	R _{VBAT}	0	0 to 100	kΩ
12	C _{VC2}	0.047	0.047 to 0.22 ^{*1}	μF
13	C _{VC3}	0.047	0.047 to 0.22 ^{*1}	μF
14	C _{VSS}	4.7	2.2 to 10 ^{*1}	μF
15	C _{CCT}	0.1	More than 0.01	μF
16	C _{CDT}	0.1	More than 0.02	μF
17	C _{VREG}	4.7	0.68 to 10	μF

*1. Please set up a filter constant to be $R_{VSS} \times C_{VSS} \ge 22 \ \mu F \bullet \Omega$ and to be $R_{VC2} \times C_{VC2} = R_{VC3} \times C_{VC3} = R_{VSS} \times C_{VSS}$.

Caution1. No resistance should be inserted in the power supply pin VDD.

- 2. The above constants are subject to change without prior notice.
- 3. It has not been confirmed whether the operation is normal or not in circuits other than the above example of connection. In addition, the example of connection shown above and the constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

2. S-8243B Series

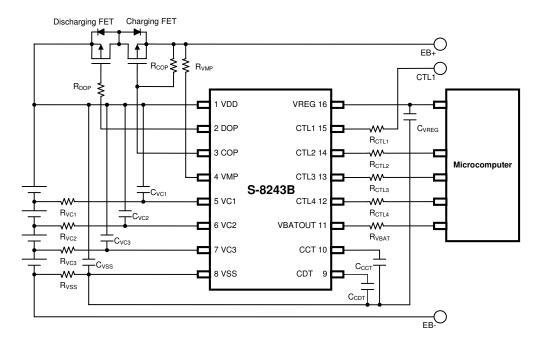




 Table 12 Constants for External Components

No.	Part	Тур.	Range	Unit
1		1	0.51 to 1 ^{*1}	kΩ
	R _{VC1}			
2	R _{VC2}	1	0.51 to 1 ^{*1}	kΩ
3	R _{VC3}	1	0.51 to 1 ^{*1}	kΩ
4	R _{VSS}	10	2.2 to 10 ^{*1}	Ω
5	R _{DOP}	5.1	2 to 10	kΩ
6	R _{COP}	1	0.1 to 1	MΩ
7	R _{VMP}	5.1	1 to 10	kΩ
8	R _{CTL1}	1	1 to 100	kΩ
9	R _{CTL2}	1	1 to 10	kΩ
10	R _{CTL3}	1	1 to 10	kΩ
11	R _{CTL4}	1	1 to 10	kΩ
12	R VBAT	0	0 to 100	kΩ
13	C _{VC1}	0.047	0.047 to 0.22 ^{*1}	μF
14	C _{VC2}	0.047	0.047 to 0.22 ^{*1}	μF
15	C _{VC3}	0.047	0.047 to 0.22 ^{*1}	μF
16	C _{VSS}	4.7	2.2 to 10 ^{*1}	μF
17	C _{CCT}	0.1	More than 0.01	μF
18	C _{CDT}	0.1	More than 0.02	μF
19	C _{VREG}	4.7	0.68 to 10	μF

*1. Please set up a filter constant to be $R_{VSS} \times C_{VSS} \ge 22 \ \mu F \bullet \Omega$ and to be $R_{VC1} \times C_{VC1} = R_{VC2} \times C_{VC2} = R_{VC3} \times C_{VC3} = R_{VSS} \times C_{VSS}$.

Caution1. No resistance should be inserted in the power supply pin VDD.

- 2. The above constants are subject to change without prior notice.
- 3. It has not been confirmed whether the operation is normal or not in circuits other than the above example of connection. In addition, the example of connection shown above and the constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

Precautions

- Pay attention to the operating conditions for input/output voltage and load current so that the power loss in the IC does not exceed the package power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- Seiko Instruments Inc. shall not be responsible for any patent infringement by products including the S-8243 series, the method of using the S-8243 series in such products, the product specifications or the country of destination thereof.

■ The Example of Application Circuit

1. S-8243A Series

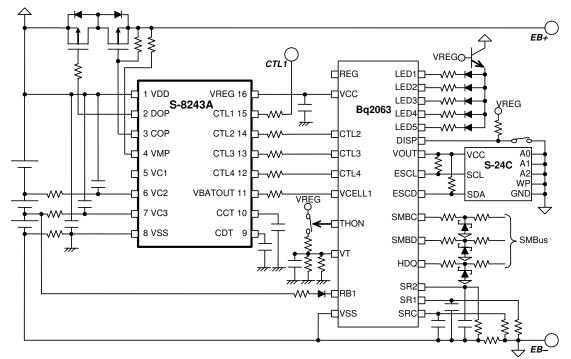
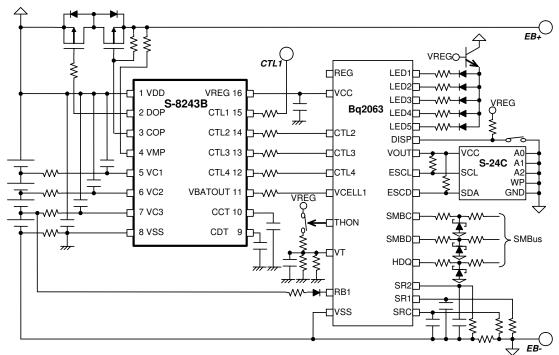


Figure 12

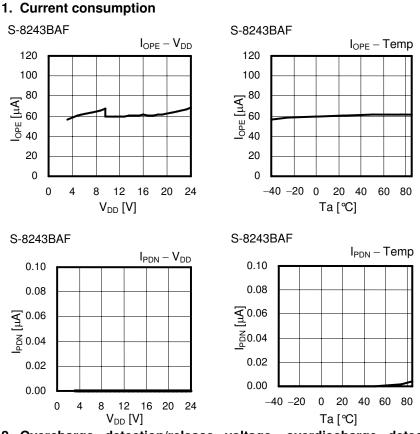
2. S-8243B Series



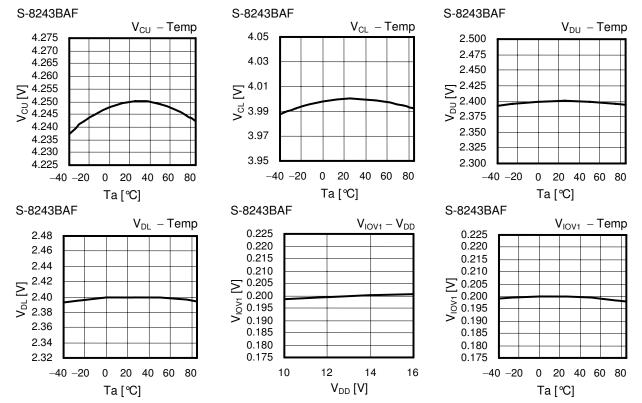


Caution The above connection example will not guarantee successful operation. Perform thorough evaluation using the actual application.

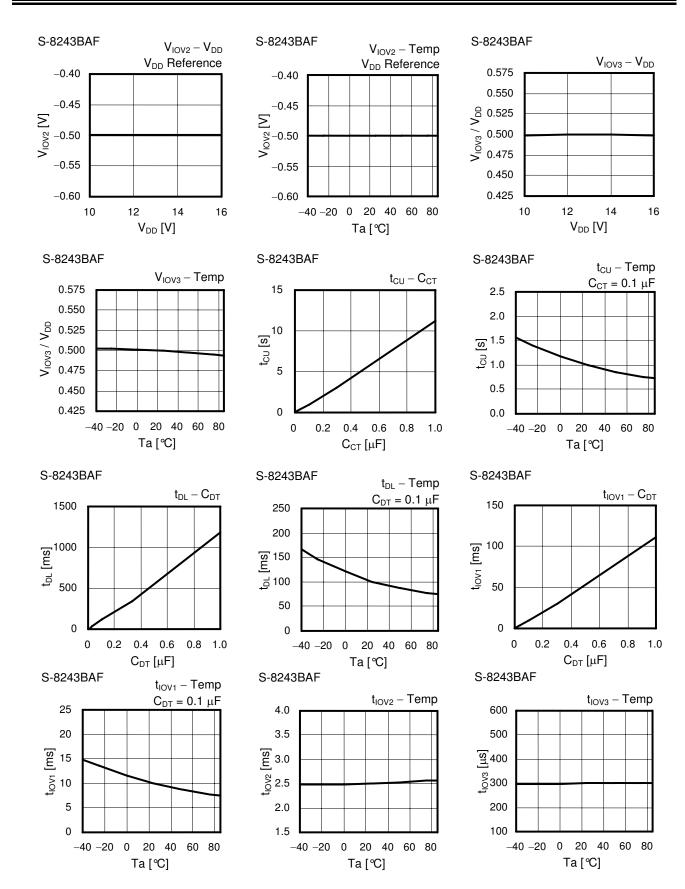
Characteristics (Typical Data)

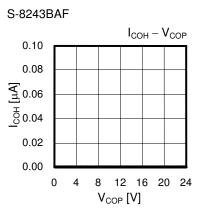


2. Overcharge detection/release voltage, overdischarge detection/release voltage, overcurrent detection voltages, and delay times

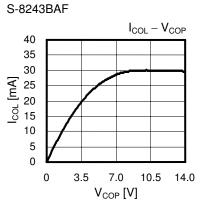


BATTERY PROTECTION IC FOR 3-SERIAL OR 4-SERIAL CELL PACK S-8243A/B Series

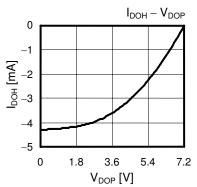


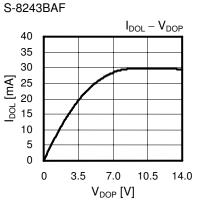






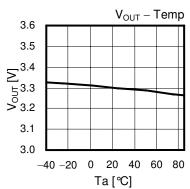
S-8243BAF

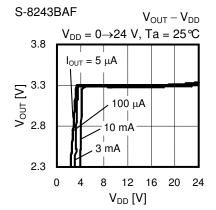


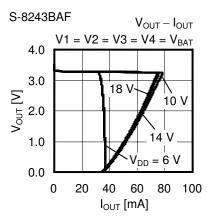


4. Voltage regulator

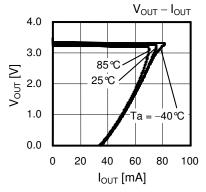




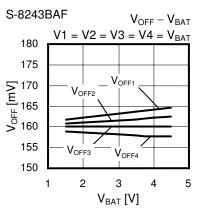


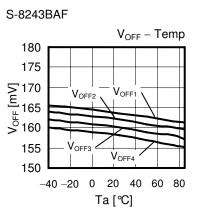


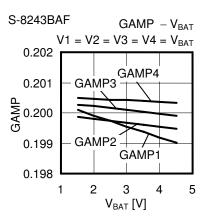
S-8243BAF



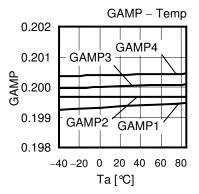
5. Battery monitor amp

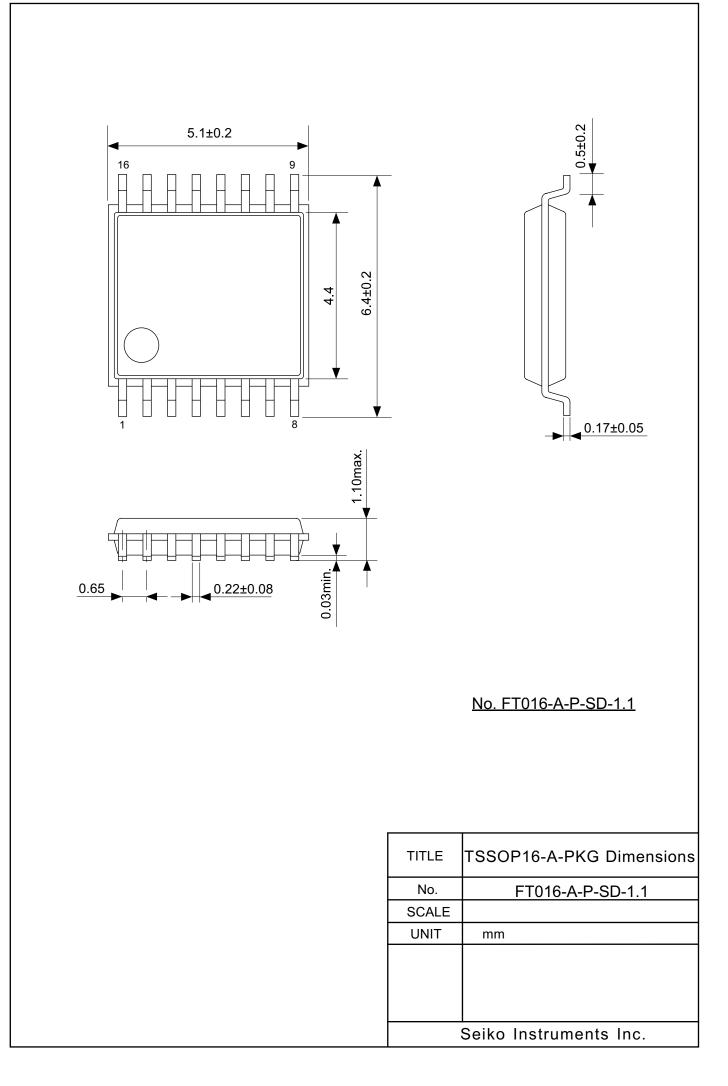


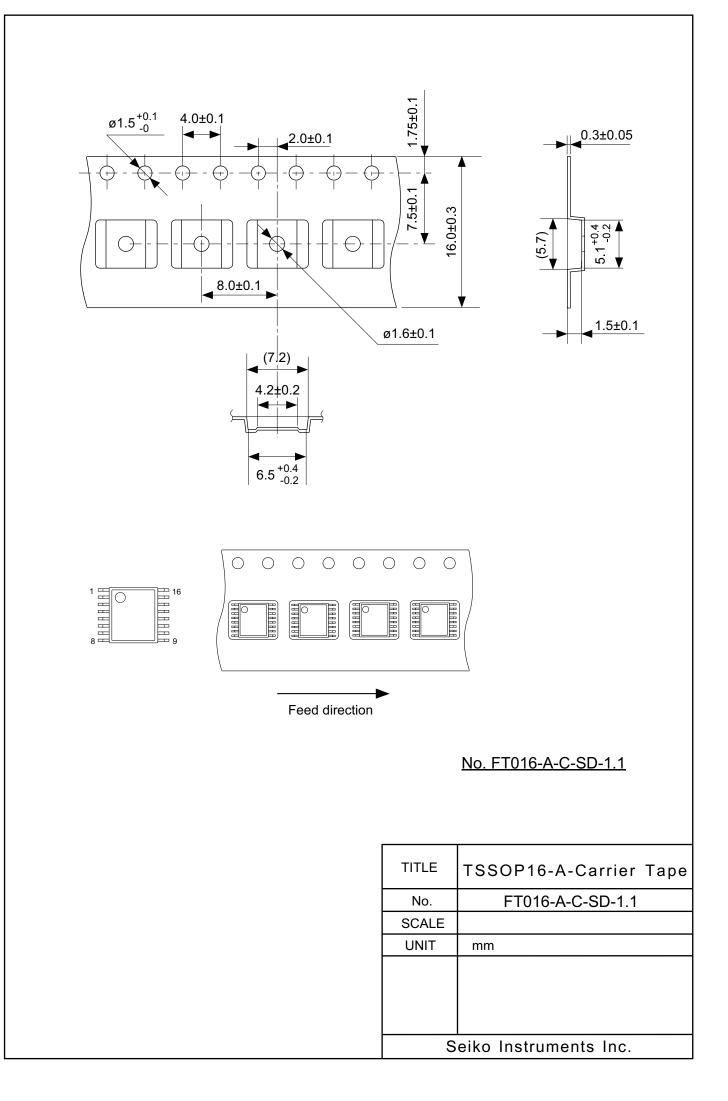


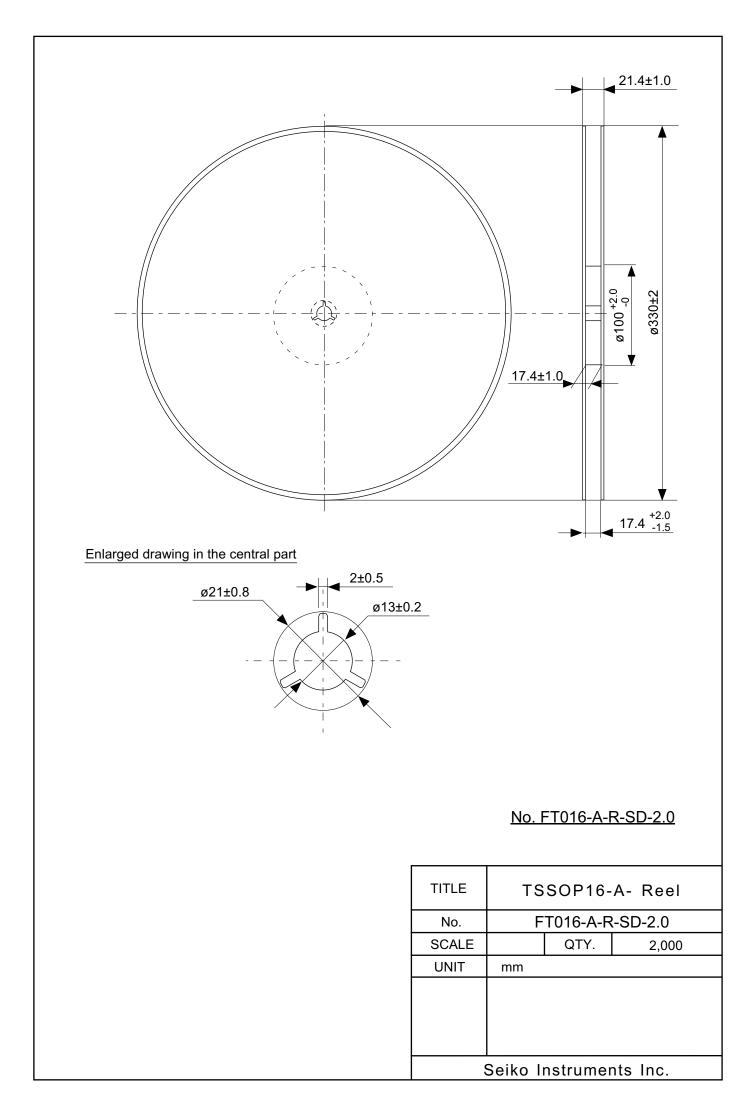


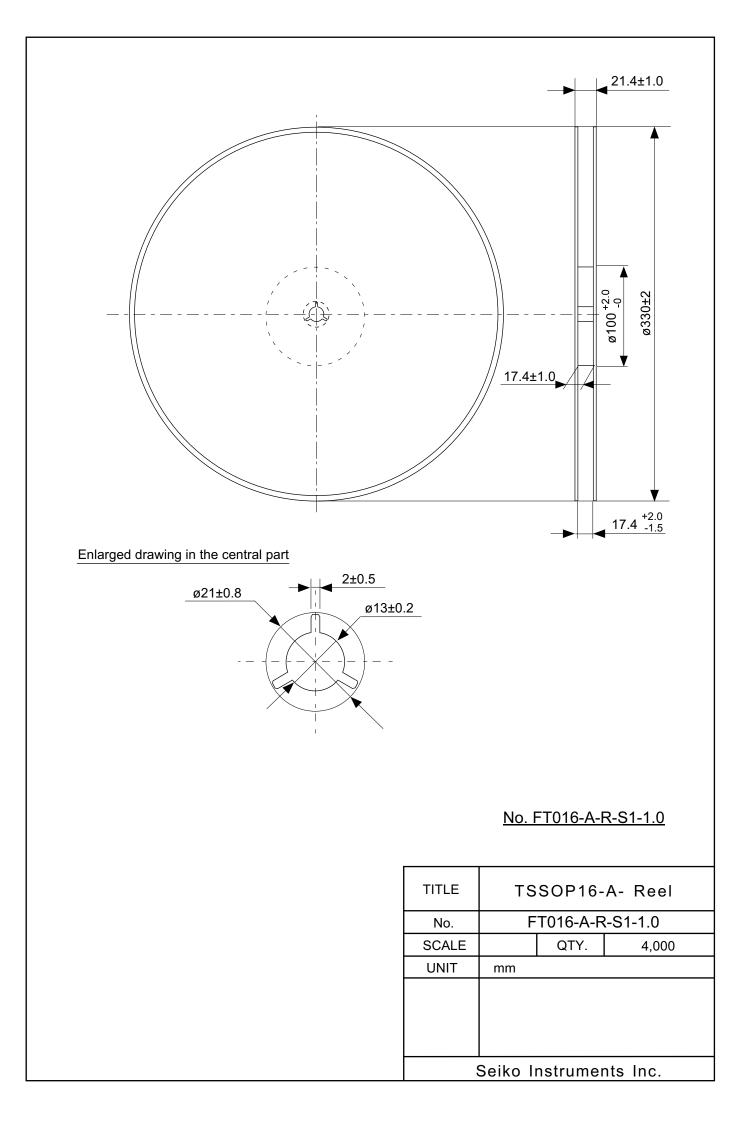
S-8243BAF













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